

## EAST Search History

## EAST Search History (Prior Art)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	0	257/77,335,402,403,404,E29.027,E29.066,E29.256,E29.258,E29.261.ccls. and (SiC or (silicon near carbide)) and DMOS near (FET or transistor) and (impurity near concentration) with profile and @ad<"20050225"	US-PGPUB; USPAT	OR	ON	2009/08/13 11:59
L2	0	257/77,335,402,403,404,E29.027,E29.066,E29.256,E29.258,E29.261.ccls. and (SiC or (silicon near carbide)) and DMOS near (FET or transistor) and (impurity near concentration) with profile and @ad<"20050225"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/08/13 12:00
S1	1089	257/77.ccls.	US-PGPUB; USPAT	OR	ON	2008/02/22 12:05
S2	72	257/77.ccls. and (impurity or dop \$3) with low near10 (surface or top)	US-PGPUB; USPAT	OR	ON	2008/02/22 12:08
S3	81	257/77.ccls. and (impurity or dop \$3) near3 profile	US-PGPUB; USPAT	OR	ON	2008/02/22 12:28
S4	11	257/77.ccls. and graded near8 (impurity or dop\$3) near3 profile	US-PGPUB; USPAT	OR	ON	2008/02/22 12:29
S5	35	257/77.ccls. and drift adj layer near10 epitaxial	US-PGPUB; USPAT	OR	ON	2008/02/22 15:40
S6	0	single adj step near5 ion adj implantation and MOS	US-PGPUB; USPAT	OR	ON	2008/02/22 16:29
S7	17	single adj step near5 ion adj implantation and MOS	US-PGPUB; USPAT	OR	ON	2008/02/22 16:29
S8	28	single adj step with ion adj implantation and MOS	US-PGPUB; USPAT	OR	ON	2008/02/22 16:33
S9	28	(single adj step or single-step) with ion adj implantation and MOS	US-PGPUB; USPAT	OR	ON	2008/02/22 16:33
S10	2	"20040119076"	US-PGPUB; USPAT	OR	ON	2008/09/18 18:13
S11	1	(silicon adj carbide or epitaxial) with (single-step or single adj step) near5 ion near implant\$5 and implantation adj energy and @ad<"20040227"	US-PGPUB; USPAT	OR	ON	2008/09/18 18:20
S12	13	(single-step or single adj step) near5 ion near implant\$5 and implantation adj energy and @ad<"20040227"	US-PGPUB; USPAT	OR	ON	2008/09/18 18:31

S13	20	constant near5 implantation adj energy and @ad<"20040227"	US-PGPUB; USPAT	OR	ON	2008/09/18 18:37
S14	10	accumulation same mobility near10 (improv\$3 or increas\$3) and silicon adj carbide and @ad<"20040227"	US-PGPUB; USPAT	OR	ON	2009/01/07 17:56
S15	4	("20040238883"   "6228725"   "6455892"   "6784492").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2009/01/07 18:17
S16	450	257/335,548,549,e21.056,e21.054, e21.065.ccls. and ((impurity or dopant or doping) near10 (profile or gradient or vary\$3 or higher or lower or non-uniform or nonuniform) or (high or highly) near (concentration or concentrated) or (nonuniformly or non-uniformly) near (doped)) and @ad<"20040227" and (metal adj oxide adj semiconductor or MOS or MOSFET or metal adj insulator adj semiconductor or MIS)	US-PGPUB; USPAT	OR	ON	2009/07/28 17:49
S17	70	257/335,548,549,e21.056,e21.054, e21.065.ccls. and ((impurity or dopant or doping) near10 (profile or gradient or vary\$3 or higher or lower or non-uniform or nonuniform) or (high or highly) near (concentration or concentrated) or (nonuniformly or non-uniformly) near (doped)) and @ad<"20040227" and (metal adj oxide adj semiconductor or MOS or MOSFET or metal adj insulator adj semiconductor or MIS) and (silicon adj carbide or SiC)	US-PGPUB; USPAT	OR	ON	2009/07/28 17:50
S18	1	10/588103	US-PGPUB; USPAT	OR	ON	2009/07/28 18:07
S19	9	("4487639"   "4868626"   "4881119"   "4935799"   "5065213"   "5118635"   "5247200"   "5380670"   "5424231").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2009/07/28 19:05
S20	0	257/335,548,549,e21.056,e21.054, e21.065.ccls. and ((impurity or dopant or doping) near10 (profile or gradient or vary\$3 or higher or lower or non-uniform or nonuniform) or (high or highly) near (concentration or concentrated) or (nonuniformly or non-uniformly) near (doped)) and @ad<"20040227" and (metal adj oxide adj semiconductor or MOS or MOSFET or metal adj insulator adj semiconductor or MIS) and (silicon adj carbide or SiC)	USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/28 19:10

S21	14	((impurity or dopant or doping) near10 (profile or gradient or vary \$3 or higher or lower or non-uniform or nonuniform) or (high or highly) near (concentration or concentrated) or (nonuniformly or non-uniformly) near (doped)) with channel and @ad<"20040227" and (metal adj oxide adj semiconductor or MOS or MOSFET or metal adj insulator adj semiconductor or MIS) and (silicon adj carbide or SiC)	USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/28 19:10
S22	14	S21 not S17	USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/28 19:10
S23	590	((impurity or dopant or doping) near10 (profile or gradient or vary \$3 or higher or lower or non-uniform or nonuniform) or (high or highly) near (concentration or concentrated) or (nonuniformly or non-uniformly) near (doped)) with channel and @ad<"20040227" and (metal adj oxide adj semiconductor or MOS or MOSFET or metal adj insulator adj semiconductor or MIS) and (silicon adj carbide or SiC)	US-PGPUB; USPAT	OR	ON	2009/07/28 19:13
S24	589	((impurity or dopant or doping) near10 (profile or gradient or vary \$3 or higher or lower or non-uniform or nonuniform) or (high near concentration or highly near concentrated) or (nonuniformly or non-uniformly) near (doped)) with channel and @ad<"20040227" and (metal adj oxide adj semiconductor or MOS or MOSFET or metal adj insulator adj semiconductor or MIS) and (silicon adj carbide or SiC)	US-PGPUB; USPAT	OR	ON	2009/07/28 19:14
S25	571	S24 not S17	US-PGPUB; USPAT	OR	ON	2009/07/28 19:14

S26	50	((impurity or dopant or doping) near10 (profile or gradient or vary \$3 or higher or lower or non-uniform or nonuniform) or (high near concentration or highly near concentrated) or (nonuniformly or non-uniformly) near (doped)) with channel and @ad<"20040227" and (metal adj oxide adj semiconductor or MOS or MOSFET or metal adj insulator adj semiconductor or MIS) and (silicon adj carbide or SiC) near8 epitaxial	US-PGPUB; USPAT	OR	ON	2009/07/28 19:15
S27	44	S26 not S17	US-PGPUB; USPAT	OR	ON	2009/07/28 19:15
S28	3	(miura-mineo.in. or rohm.as.) and ((metal adj oxide adj semiconductor or MOS or MOSFET) and (silicon adj carbide or SiC) and channel with (low\$2 or high\$2) with (impurity or dopant))	US-PGPUB; USPAT	OR	ON	2009/07/28 19:26
S29	11	("20020038891"   "20020172774"   "20040036113"   "20040119076"   "20040159886"   "4827319"   "5976936"   "6020600"   "6373102"   "6573534"   "6639273").PN.	US-PGPUB; USPAT	OR	ON	2009/07/28 19:27
S31	1	"6573534".pn.	US-PGPUB; USPAT	OR	ON	2009/07/29 12:04
S32	21	("4859621"   "5170231"   "5233215"   "5323040"   "5389799"   "5396085"   "5399515"   "5451797"   "5459107"   "5460985"   "5506421"   "5514604"   "5543637"   "5574295"   "5614749"   "5629531"   "5681762"   "5723376"   "5773849"   "5776837"   "6020600").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2009/07/29 12:10
S33	1	(nonuniformly near doped or non-uniformly near3 concentration) and @ad<"20050225" and (metal adj oxide adj semiconductor or MOS or MOSFET or metal adj insulator adj semiconductor or MIS) and (silicon adj carbide or SiC) near8 epitaxial	US-PGPUB; USPAT	OR	ON	2009/07/29 12:59
S34	128	((impurity or dopant or doping) near10 (profile or gradient or vary \$3 or retrograde)) and @ad<"20050225" and (metal adj oxide adj semiconductor or MOS or MOSFET or metal adj insulator adj semiconductor or MIS) and (silicon adj carbide or SiC) near8 epitaxial	US-PGPUB; USPAT	OR	ON	2009/07/29 13:01

S35	1	"6455892".pn.	US-PGPUB; USPAT	OR	ON	2009/08/07 11:53
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**EAST Search History (Interference)**

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S30	8	((metal adj oxide adj semiconductor or MOS or MOSFET) and (silicon adj carbide or SiC) and channel with (low\$2 or high\$2) with (impurity or dopant)).clm.	US-PGPUB	OR	ON	2009/07/28 19:23

**8/ 13/ 2009 12:01:42 PM****C:\ Documents and Settings\ fyeunglopez\ My Documents\ EAST\ Workspaces\ 10588103.wsp**